

MOSFETs Silicon P-Channel MOS (U-MOSVI)

XPN9R614MC

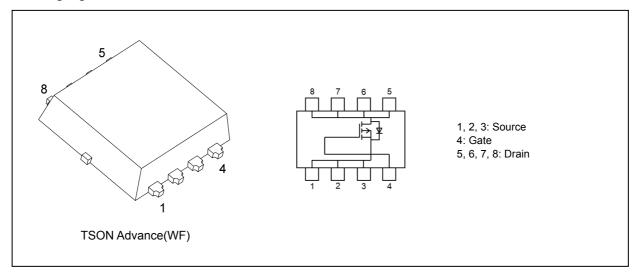
1. Applications

- · Automotive
- Switching Voltage Regulators
- · DC-DC Converters
- · Motor Drivers

2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 7.4 \text{ m}\Omega$ (typ.) ($V_{GS} = -10 \text{ V}$)
- (4) Low leakage current: $I_{DSS} = -10 \mu A (max) (V_{DS} = -40 V)$
- (5) Enhancement mode: V_{th} = -1.0 to -2.1 V (V_{DS} = -10 V, I_D = -0.5 mA)

3. Packaging and Internal Circuit



1



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Character	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	-40	V
Gate-source voltage			V _{GSS}	+10/-20	
Drain current (DC)		(Note 1)	I _D	-40	Α
Drain current (pulsed)		(Note 1)	I _{DP}	-80	
Power dissipation	(T _c = 25 °C)		P _D	100	W
Power dissipation	(t = 10 s)	(Note 2)		2.27]
Power dissipation	(t = 10 s)	(Note 3)		0.84	Ī
Single-pulse avalanche energy		(Note 4)	E _{AS}	67	mJ
Single-pulse avalanche current			I _{AS}	-40	Α
Channel temperature		(Note 5)	T _{ch}	175	°C
Storage temperature		(Note 5)	T _{stg}	-55 to 175	

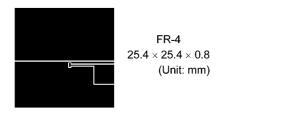
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

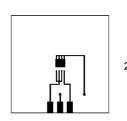
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal impedance	(T _c = 25 °C)		Z _{th(ch-c)}	1.5	°C/W
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 2)	Z _{th(ch-a)}	66	
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 3)	Z _{th(ch-a)}	178	

- Note 1: Ensure that the channel temperature does not exceed 175 °C.
- Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1
- Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2
- Note 4: V_{DD} = -25 V, T_{ch} = 25 °C (initial), L = 43 μ H, R_{G} = 25 Ω , I_{AS} = -40 A, V_{GS} = 0/-15 V
- Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.





FR-4 $25.4 \times 25.4 \times 0.8$ (Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V _{GS} = +10/-20 V, V _{DS} = 0 V	_	_	±1	μА
Drain cut-off current	I _{DSS}	$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}$	_		-10	
Drain-source breakdown voltage	V _{(BR)DSS}	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-40			V
	V _{(BR)DSX}	I _D = -10 mA, V _{GS} = 10 V	-30			
Gate threshold voltage	V_{th}	$V_{DS} = -10 \text{ V}, I_{D} = -0.5 \text{ mA}$	-1.0		-2.1	
Drain-source on-resistance	R _{DS(ON)}	V_{GS} = -4.5 V, I_D = -20 A	_	9.6	13.4	mΩ
		$V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	_	7.4	9.6	

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	3000	_	pF
Reverse transfer capacitance	C _{rss}		_	335	_	
Output capacitance	C _{oss}		_	410		
Gate resistance	r _g		_	13		Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	35	_	ns
Switching time (turn-on time)	t _{on}		_	50		
Switching time (fall time)	t _f		_	165	_	
Switching time (turn-off time)	t _{off}		_	570	1	

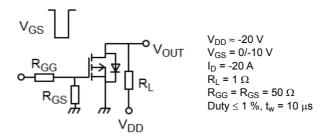


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx -32 \text{ V}, V_{GS} = -10 \text{ V},$ $I_{D} = -40 \text{ A}$	_	64		nC
Gate-source charge 1	Q _{gs1}		_	8		
Gate-drain charge	Q_{gd}		_	17	_	

6.4. Source-Drain Characteristics ($T_a = 25$ °C unless otherwise specified)

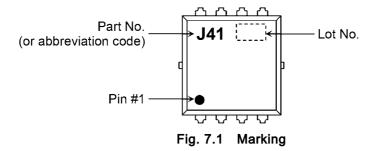
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 6)	I _{DR}	_	_	_	-40	Α
Reverse drain current (pulsed)	(Note 6)	I _{DRP}	_		_	-80	Α
Diode forward voltage		V_{DSF}	$I_{DR} = -40 \text{ A}, V_{GS} = 0 \text{ V}$		_	1.2	V

Note 6: Ensure that the channel temperature does not exceed 175 °C.

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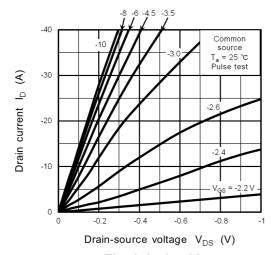


7. Marking





8. Characteristics Curves (Note)





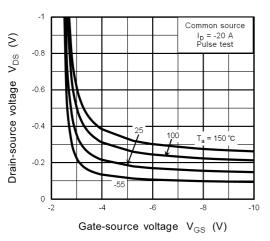


Fig. 8.3 V_{DS} - V_{GS}

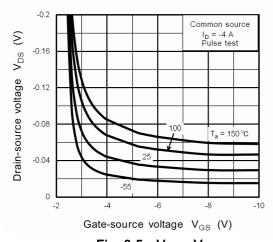


Fig. 8.5 V_{DS} - V_{GS}

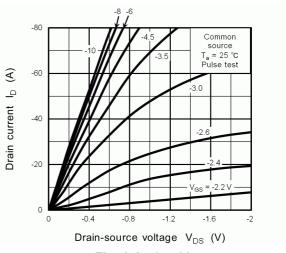


Fig. 8.2 I_D - V_{DS}

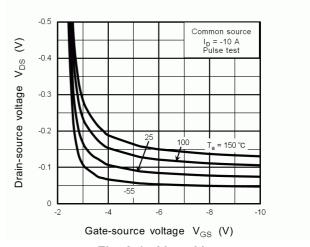


Fig. 8.4 V_{DS} - V_{GS}

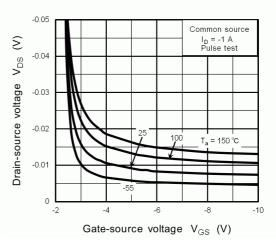


Fig. 8.6 V_{DS} - V_{GS}



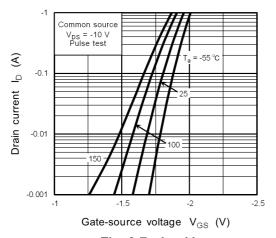


Fig. 8.7 $I_D - V_{GS}$

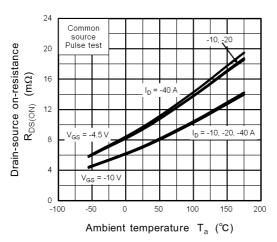


Fig. 8.9 R_{DS(ON)} - T_a

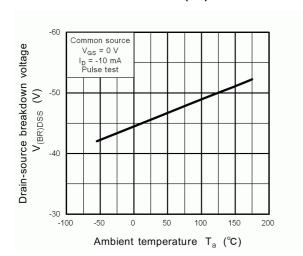


Fig. 8.11 V_{(BR)DSS} - T_a

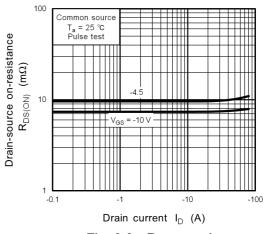


Fig. 8.8 R_{DS(ON)} - I_D

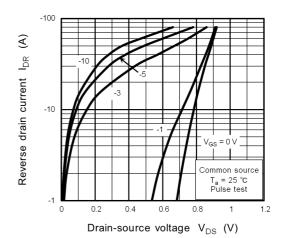


Fig. 8.10 IDR - VDS

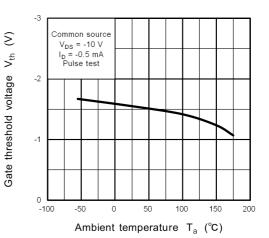
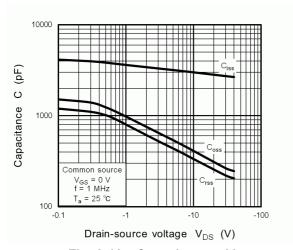


Fig. 8.12 V_{th} - T_a







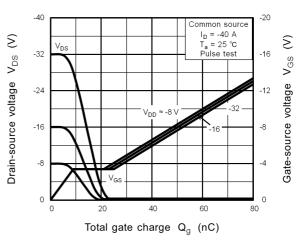


Fig. 8.14 Dynamic Input/Output Characteristics



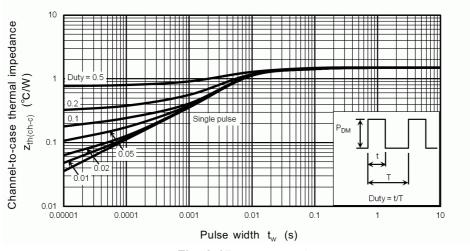
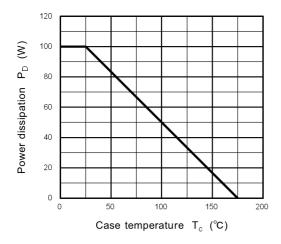


Fig. 8.15 $z_{th(ch-c)} - t_w$ (Guaranteed Maximum)



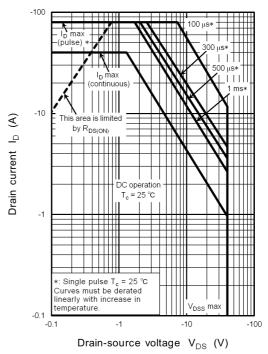


Fig. 8.16 P_D - T_c (Guaranteed Maximum)

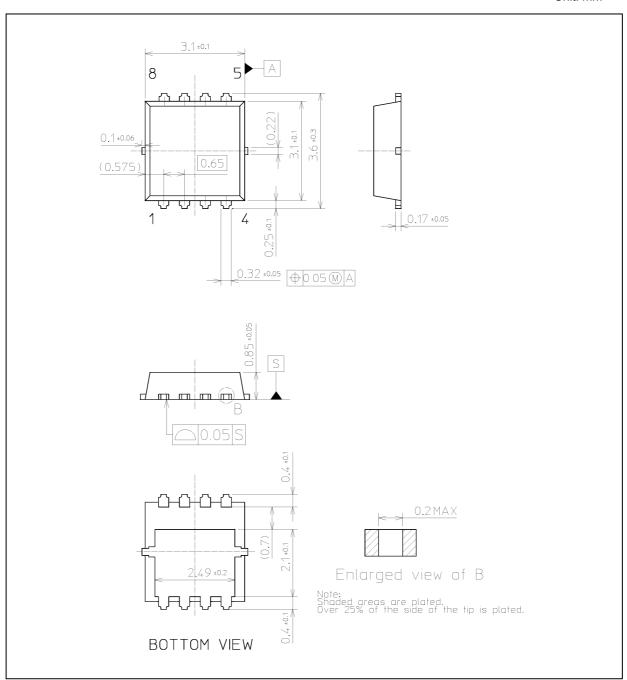
Fig. 8.17 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.029 g (typ.)

Package Name(s)			
TOSHIBA: 2-3X2A			
Nickname: TSON Advance(WF)			



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